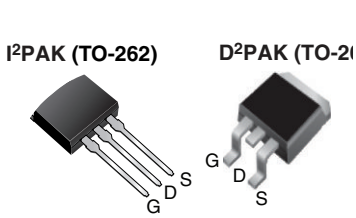
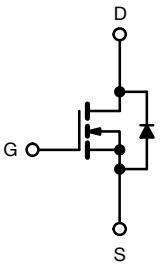
Power MOSFET





N-Channel MOSFET

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS* Available

HALOGEN FREE Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

PRODUCT SUMMARY		
V_{DS} (V)	800	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	3.0
Q_g max. (nC)	78	
Q_{gs} (nC)	9.6	
Q_{gd} (nC)	45	
Configuration	Single	

ORDERING INFORMATION			
Package	D^2PAK (TO-263)	D^2PAK (TO-263)	I^2PAK (TO-262)
Lead (Pb)-free and Halogen-free	SiHFBE30S-GE3	SiHFBE30STRL-GE3 [a]	SiHFBE30L-GE3
Lead (Pb)-free	IRFBE30SPbF	IRFBE30STRLPbF [a]	IRFBE30LPbF

Note

a. See device orientation

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	800	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V_{GS} at 10 V	T_C = 25 °C	I_D	4.1	A
		T_C = 100 °C		2.6	
Pulsed Drain Current [a]			I_{DM}	16	
Linear Derating Factor				1.0	W/°C
Single Pulse Avalanche Energy [b]			E_{AS}	260	mJ
Avalanche Current [a]			I_{AR}	4.1	A
Repetitive Avalanche Energy [a]			E_{AR}	13	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	125	W
Peak Diode Recovery dV/dt [c]			dV/dt	2.0	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	-55 to +150	°C
Soldering Recommendations (Peak temperature) [d]	for 10 s			300	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. V_{DD} = 50 V, starting T_J = 25 °C, L = 29 mH, R_g = 25 Ω, I_{AS} = 4.1 A (see fig. 12)
c. I_{SD} ≤ 4.1 A, dI/dt ≤ 100 A/µs, V_{DD} ≤ 600 V, T_J ≤ 150 °C
d. 1.6 mm from case

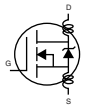
For technical questions, contact: hvm@vishay.com

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THERMAL RESISTANCE RATINGS					
PARAMETER	**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	-	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	-	1.0	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material)

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	800	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA	-	0.90	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 800 V, V_{GS} = 0 V	-	-	100	µA
		V_{DS} = 640 V, V_{GS} = 0 V, T_J = 125 °C	-	-	500	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V; I_D = 2.5 A [b]	-	-	3.0	Ω
Forward Transconductance	g_{fs}	V_{DS} = 100 V, I_D = 2.5 A	2.5	-	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5	-	1300	-	pF
Output Capacitance	C_{oss}		-	310	-	
Reverse Transfer Capacitance	C_{rss}		-	190	-	
Total Gate Charge	Q_g	V_{GS} = 10 V; I_D = 4.1 A, V_{DS} = 400 V, see fig. 6 and 13 [b]	-	-	78	nC
Gate-Source Charge	Q_{gs}		-	-	9.6	
Gate-Drain Charge	Q_{gd}		-	-	45	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 400 V, I_D = 4.1 A, R_g = 12 Ω, R_D = 95 Ω, see fig. 10 [b]	-	12	-	ns
Rise Time	t_r		-	33	-	
Turn-Off Delay Time	$t_{d(off)}$		-	82	-	
Fall Time	t_f		-	30	-	
Gate Input Resistance	R_g	f = 1 MHz, open drain	0.6	-	1.6	Ω
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	4.1	A
Pulsed Diode Forward Current [a]	I_{SM}		-	-	16	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = 4.1 A, V_{GS} = 0 V [b]	-	-	1.8	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = 4.1 A, dI/dt = 100 A/µs [b]	-	480	720	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	1.8	2.7	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

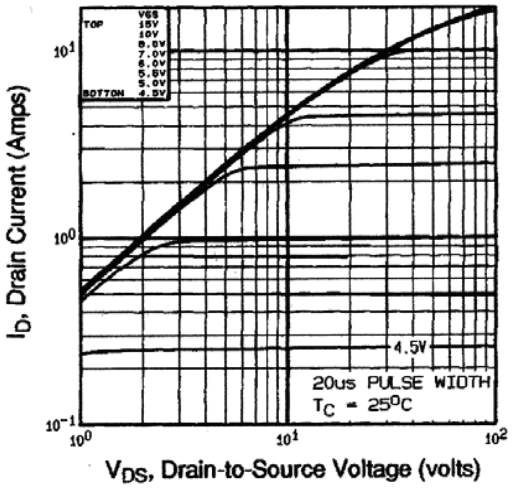


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

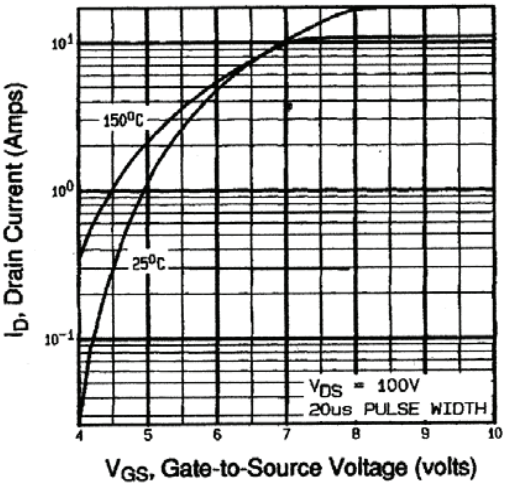


Fig. 3 - Typical Transfer Characteristics

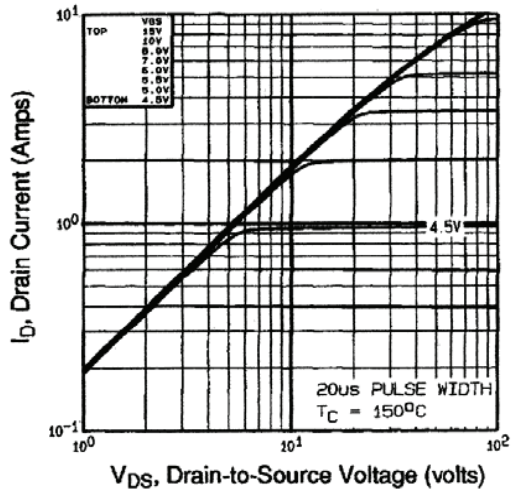


Fig. 2 - Typical Output Characteristics, T_C = 150 °C

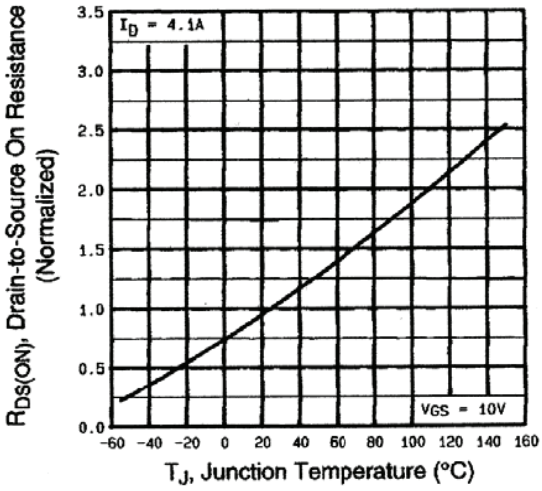


Fig. 4 - Normalized On-Resistance vs. Temperature

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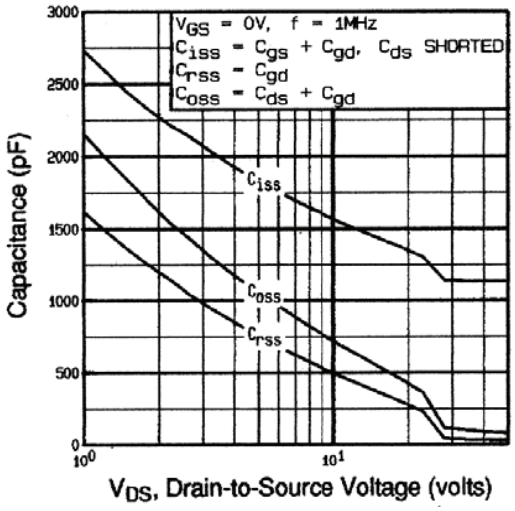


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

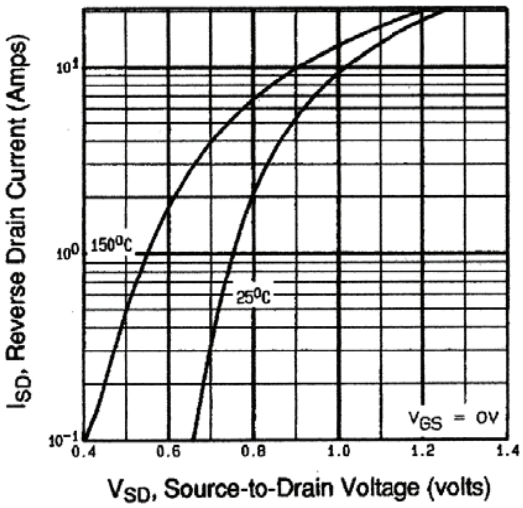


Fig. 7 - Typical Source-Drain Diode Forward Voltage

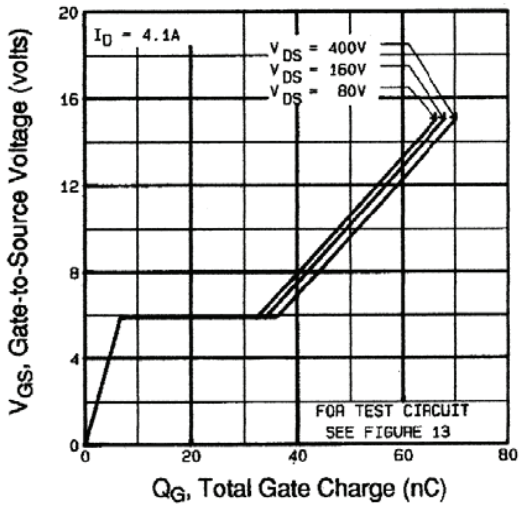


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

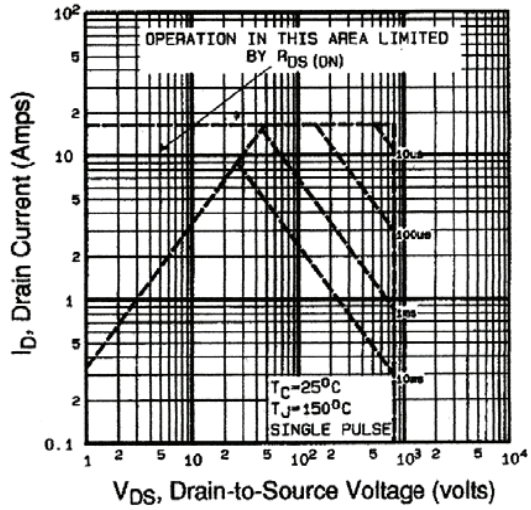


Fig. 8 - Maximum Safe Operating Area

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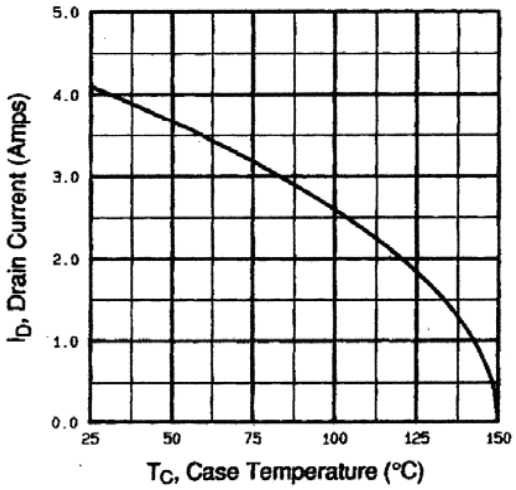


Fig. 9 - Maximum Drain Current vs. Case Temperature

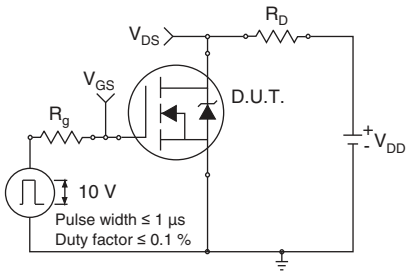


Fig. 10a - Switching Time Test Circuit

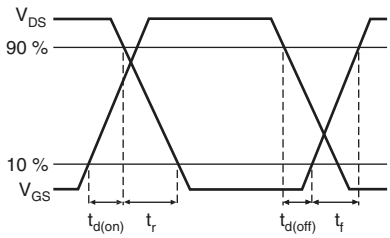


Fig. 10b - Switching Time Waveforms

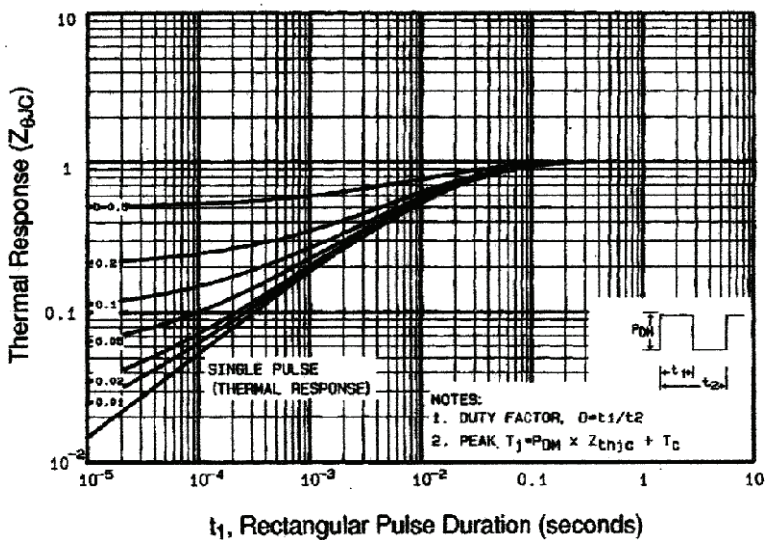


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

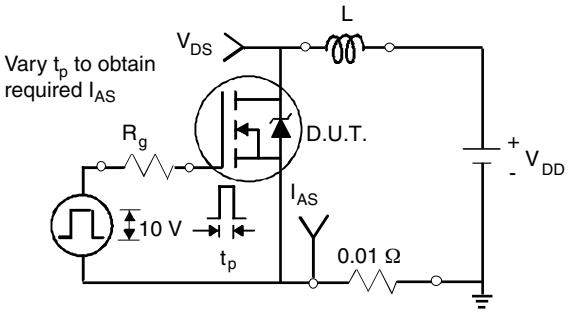


Fig. 12a - Unclamped Inductive Test Circuit

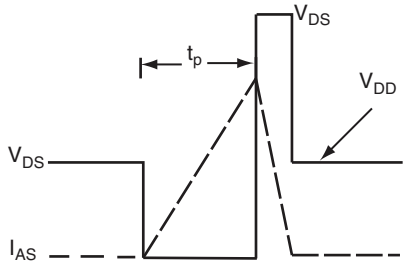


Fig. 12b - Unclamped Inductive Waveforms

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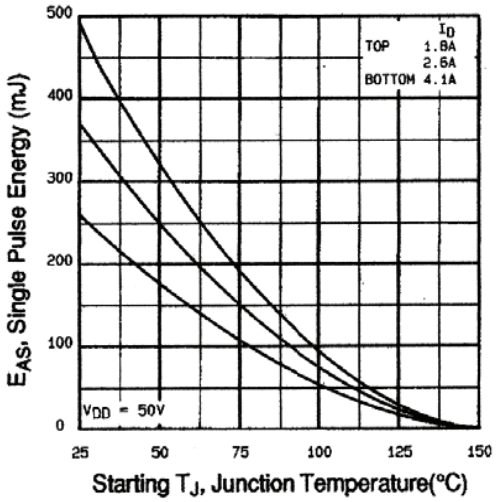


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

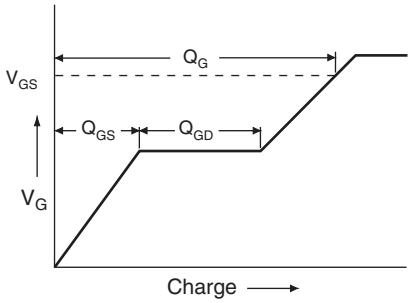


Fig. 13a - Maximum Avalanche Energy vs. Drain Current

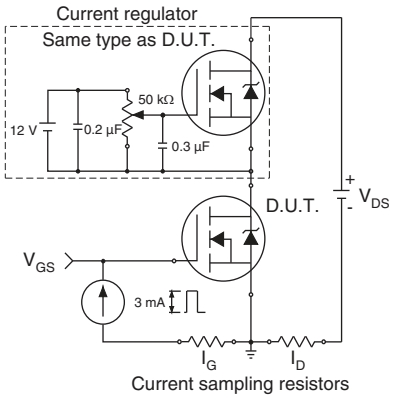
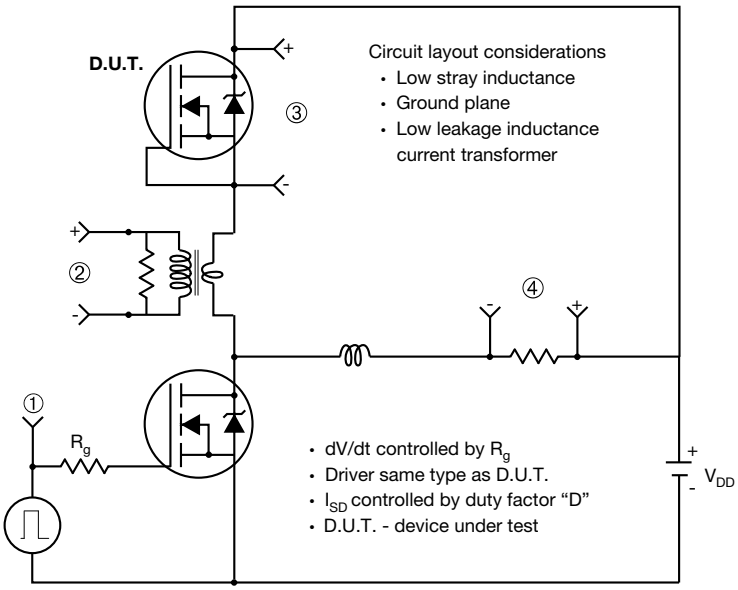
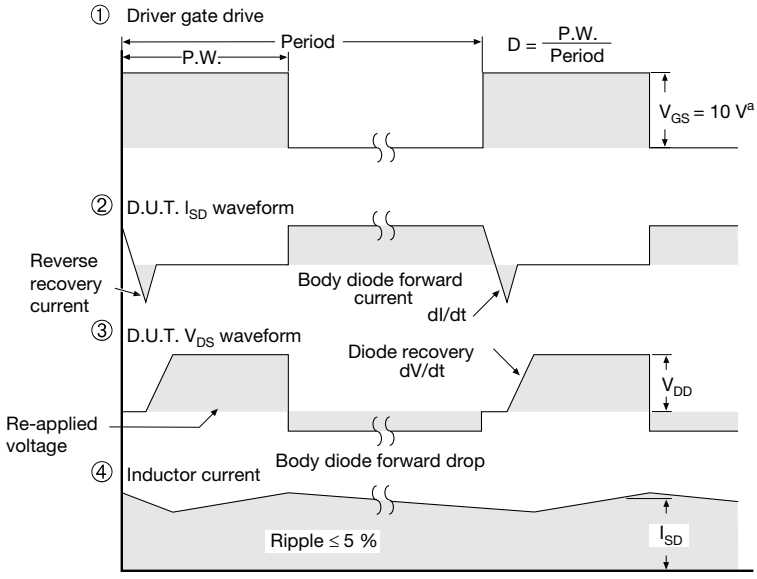


Fig. 13b - Gate Charge Test Circuit

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Peak Diode Recovery dV/dt Test Circuit





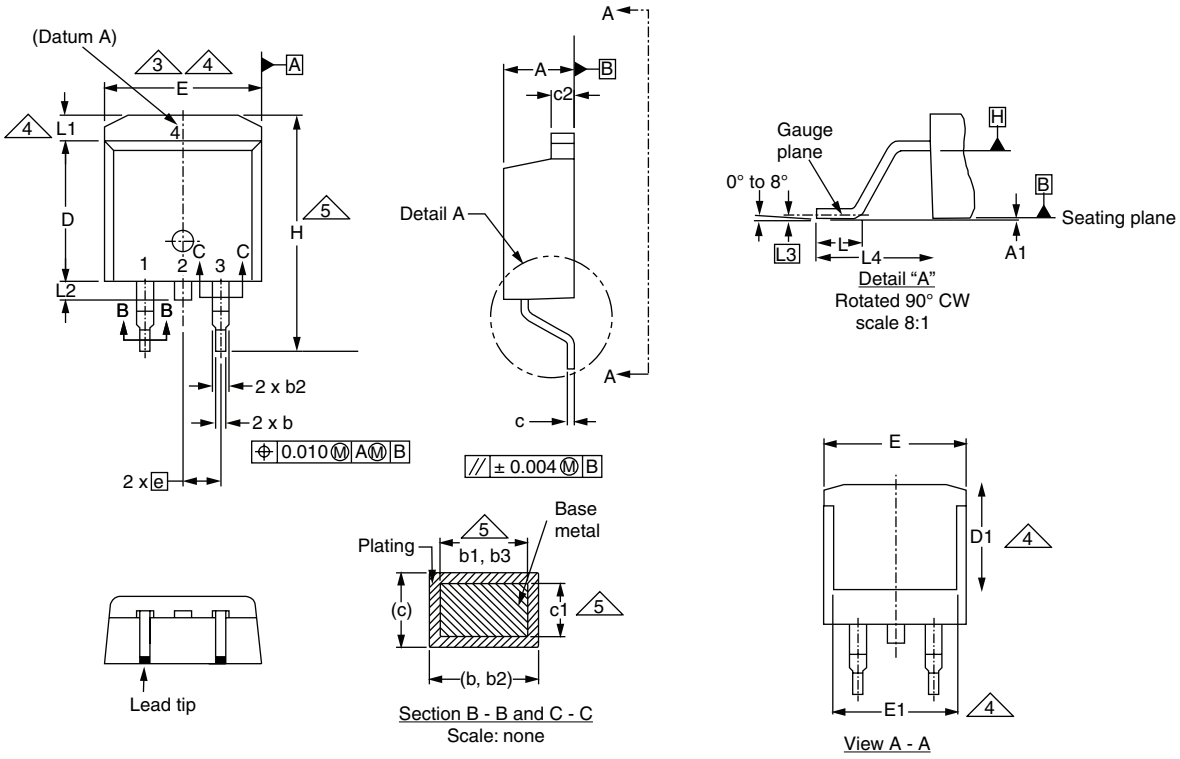
Note

a. V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel

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TO-263AB (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

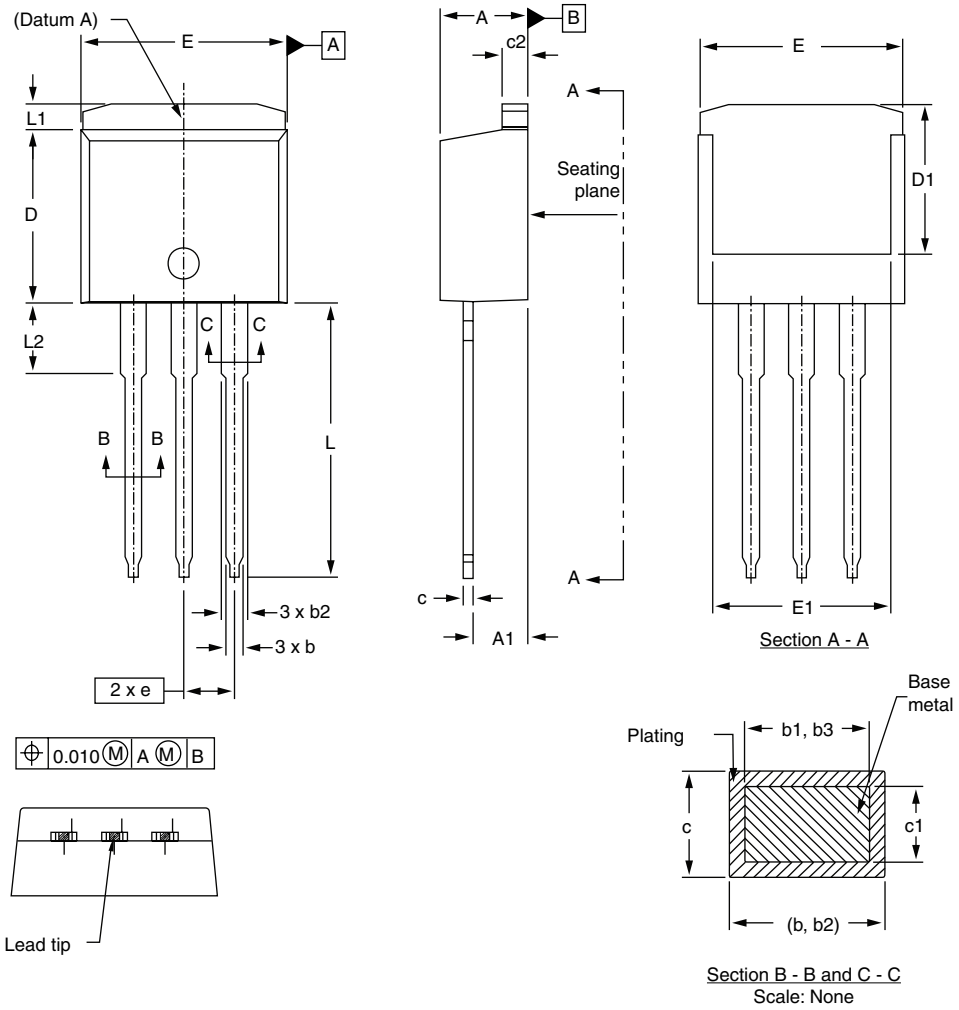
	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

I²PAK (TO-262) (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	2.03	3.02	0.080	0.119
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065

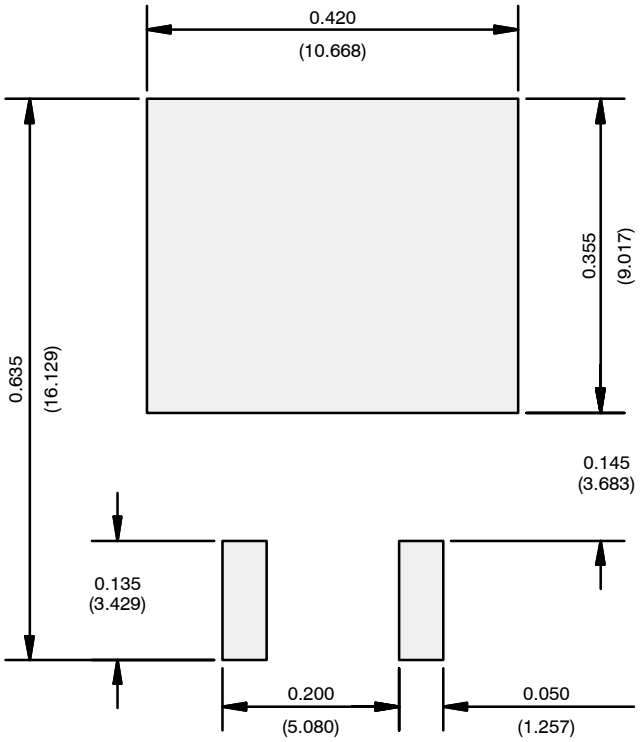
	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D	8.38	9.65	0.330	0.380
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
L	13.46	14.10	0.530	0.555
L1	-	1.65	-	0.065
L2	3.56	3.71	0.140	0.146

ECN: S-82442-Rev. A, 27-Oct-08
DWG: 5977

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outmost extremes of the plastic body.
3. Thermal pad contour optional within dimension E, L1, D1, and E1.
4. Dimension b1 and c1 apply to base metal only.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

Return to Index

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Elektronik komponent tedarikinde Entegreci

Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

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Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

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Entegreci is an online electronic components store based in Türkiye. Search by manufacturer part number to see stock, prices and datasheets for integrated circuits, microcontrollers, transistors, passive components and connectors, or request a quote for parts that are not listed.

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